

60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

54 A

Features

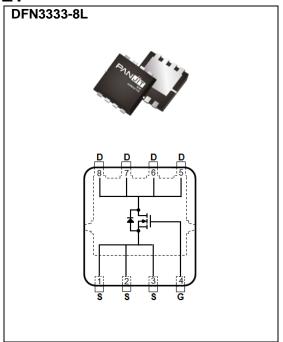
- RDS(ON), VGS@10V, ID@10A<8.4 $m\Omega$
- RDS(ON), VGS@4.5V, ID@6A<15m Ω
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current (Note 3)	T _C =25°C		54		
	T _C =100°C	I _D	38	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	216		
Power Dissipation	T _C =25°C		48	W	
	T _C =100°C	Po	24		
Continuous Drain Current (Note 4)	T _A =25°C		12		
	T _A =70°C	I _D	10	Α	
Power Dissipation	T _A =25°C	De	2.5	W	
	T _A =70°C	Pb	1.8		
Single Pulse Avalanche Current (Note 5)		I _{AS}	20	Α	
Single Pulse Avalanche Energy (Note 5)		Eas	48	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Thermal Resistance (Note 4)	Junction to Case	$R_{ heta JC}$	3.1	°C/W	
	Junction to Ambient	RθJA	60		



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	DSS V _{GS} =0V, I _D =250uA 60		-	-	.,	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1.5	2.2	3	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =10A	-	6.7	8.4	mΩ	
		V _{GS} =4.5V, I _D =6A	-	11.5	15		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
Dynamic (Note 6)	•			•			
Total Gate Charge	Q_g	V _{DS} =30V, I _D =10A,	ı	27	35	nC	
Gate-Source Charge	Qgs		ı	7	-		
Gate-Drain Charge	Q_{gd}	V _{GS} =10V (Note 2,3)	-	6	-		
Input Capacitance	Ciss	.,	-	1454	1890	pF	
Output Capacitance	Coss	V _{DS} =30V, V _{GS} =0V,	-	616	862		
Reverse Transfer Capacitance	Crss	f=1MHz	-	54	-		
Gate resistance	Rg	f=1MHz	-	1	-	Ω	
Turn-On Delay Time	td _(on)	V _{DS} =30V, I _D =10A,	-	7.8	-		
Turn-On Rise Time	tr		-	28	-		
Turn-Off Delay Time	td(off)	$V_{GS}=10V, R_{G}=3\Omega$ (Note 2,3)	-	22	-	ns	
Turn-Off Fall Time	tf	(Note 2,3)	-	50	-		
Drain-Source Diode	-				•		
Diode Forward Current	Is	T 050	-	-	54	A	
Pulsed Diode Forward Current	I _{SM}	T _C =25°C	-	-	216		
Diode Forward Voltage	V _{SD}	Is=20A, V _G s=0V	-	0.8	1.3	V	
Reverse Recovery Time	Trr	V _{DD} =30V,V _{GS} =0V	-	24	-	ns	
Reverse Recovery Charge	Qrr	I _S =20A,dI _S /dt=100A/us	-	9.2	-	nC	

NOTES:

- 1. Pulse width<100us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Chip capability with an $R_{\theta JC}$ = 3.1°C/W.
- 4. R_{BJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 5. EAS is calculated based on the condition of L=1mH, IAS=10A, VDD=30V, VGS=10V. 100% test at L=0.1mH, IAS=20A in production.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

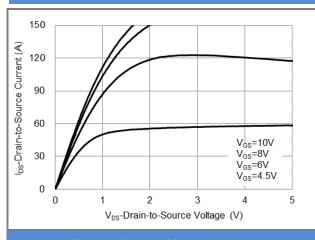


Fig.1 On-Region Characteristics

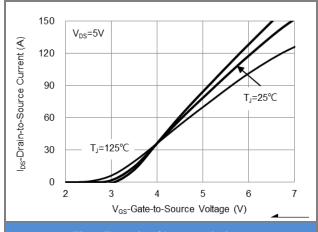


Fig.2 Transfer Characteristics

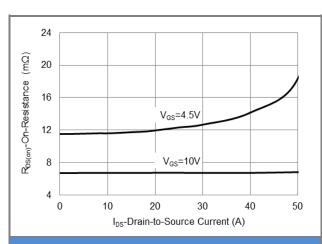


Fig.3 On-Resistance vs. Drain Current

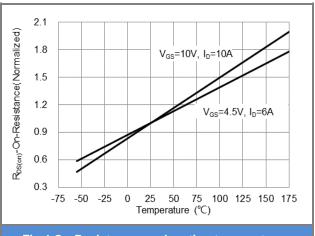
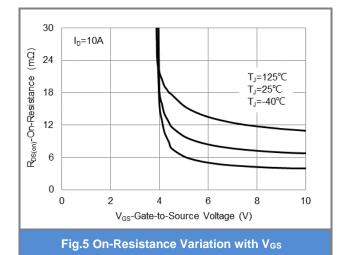


Fig.4 On-Resistance vs. Junction temperature



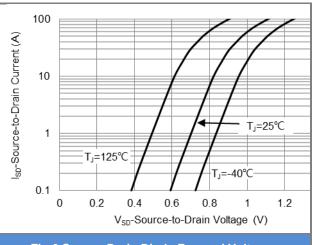


Fig.6 Source-Drain Diode Forward Voltage



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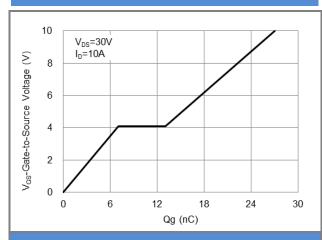


Fig.7 Gate-Charge Characteristics

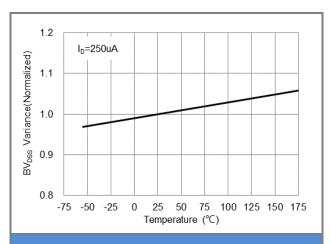


Fig.8 Breakdown Voltage Variation vs. Temperature

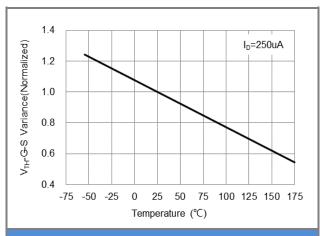


Fig.9 Threshold Voltage Variation with Temperature

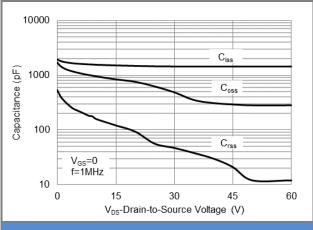
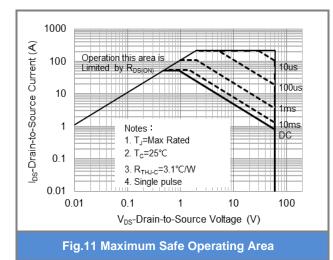


Fig.10 Capacitance vs. Drain-Source Voltage



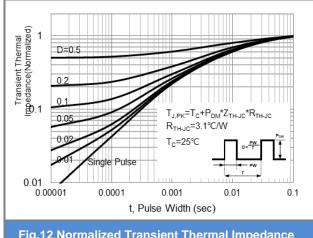


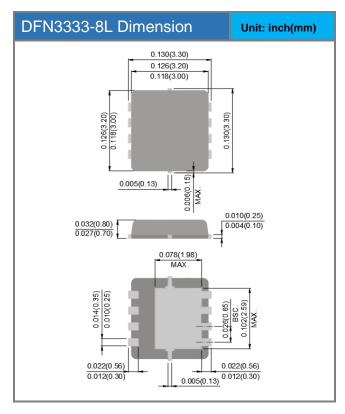
Fig.12 Normalized Transient Thermal Impedance

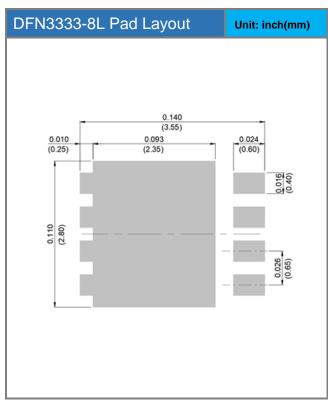


Product and Packing Information

Part No.	Package Type	Packing Type	Marking	
PJQ4564AP-AU	DFN3333-8L	5K pcs / 13" reel	564A	

Packaging Information & Mounting Pad Layout







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